Complementary Silicon Plastic Power Transistors

Designed for use in general purpose amplifier and switching applications.

Features

- High Current Gain Bandwidth Product
- Compact TO-220 AB Package
- Epoxy Meets UL94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	BD242B	BD241C BD242C	Unit
Collector-Emitter Voltage	V _{CEO}	80	100	Vdc
Collector–Emitter Voltage	V _{CES}	90	115	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current –Continuous	۱ _C	3.0		Adc
Collector Current – Peak	I _{CM}	5.0		Adc
Base Current	Ι _Β	1.0		Adc
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	40 0.32		W W/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-65 to +150		°C
ESD – Human Body Model	HBM	3	В	V
ESD – Machine Model	MM	()	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	R_{\thetaJA}	62.5	°C/W	
Thermal Resistance, Junction-to-Case	R_{\thetaJC}	3.125	°C/W	



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ORDERING INFORMATION

Device	Package	Shipping [†]
BD241CG	TO-220 (Pb-Free)	50 Units/Rail
BD242BG	TO–220 (Pb–Free)	50 Units/Rail
BD242CG	TO-220 (Pb-Free)	50 Units/Rail

⁺For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit				
OFF CHARACTERISTICS								
Collector–Emitter Sustaining Voltage (Note 1) $(I_C = 30 \text{ mAdc}, I_B = 0)$	BD242B BD241C, BD242C	V _{CEO}	80 100		Vdc			
Collector Cutoff Current $(V_{CE} = 50 \text{ Vdc}, I_B = 0)$ $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$	BD242B BD241C, BD242C	I _{CEO}		0.3	mAdc			
Collector Cutoff Current ($V_{CE} = 80 \text{ Vdc}, V_{EB} = 0$) ($V_{CE} = 100 \text{ Vdc}, V_{EB} = 0$)	BD242B BD241C, BD242C	I _{CES}		200	μAdc			
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)		I _{EBO}		1.0	mAdc			
ON CHARACTERISTICS (Note 1)								
DC Current Gain (I _C = 1.0 Adc, V _{CE} = 4.0 Vdc) (I _C = 3.0 Adc, V _{CE} = 4.0 Vdc)		h _{FE}	25 10					
Collector–Emitter Saturation Voltage $(I_C = 3.0 \text{ Adc}, I_B = 0.6 \text{ Adc})$		V _{CE(sat)}		1.2	Vdc			
Base–Emitter On Voltage ($I_C = 3.0 \text{ Adc}, V_{CE} = 4.0 \text{ Vdc}$)		$V_{BE(on)}$		1.8	Vdc			
DYNAMIC CHARACTERISTICS								
Current Gain – Bandwidth Product (Note 2) ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f_{test} = 1.0 \text{ MHz}$)		f _T	3.0		MHz			
Small–Signal Current Gain (I _C = 0.5 Adc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{fe}	20					

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

2. $f_T = |h_{fe}| \bullet f_{test}$.



Figure 1. Power Derating





SINGLE PULSE

0.1

0.2

0.5

1.0

2.0

t, TIME (ms) Figure 4. Thermal Response

0.05

0.02

0.01

0.02

0.01

0.01

Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

50

t₁

100

t₂

DUTY CYCLE, $D = t_1/t_2$

200

500 1.0 k

D CURVES APPLY FOR POWER

20

PULSE TRAIN SHOWN

 $T_{J(pk)} - T_C = P_{(pk)} Z_{\Theta JC(t)}$

10

READ TIME AT t1

5.0

The data of Figure 5 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$, $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





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